

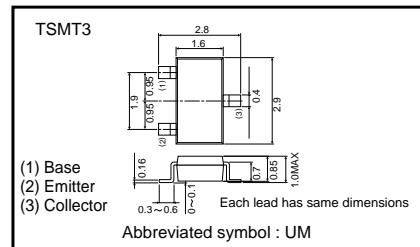
Medium power transistor (30V, 1.0A)

2SC5730

●Features

- 1) High speed switching. (T_f : Typ. : 35ns at I_c = 1.0A)
- 2) Low saturation voltage, typically
(Typ. : 150mV at I_c = 500mA, I_b = 50mA)
- 3) Strong discharge power for inductive load and
capacitance load.
- 4) Complements the 2SA2048

●External dimensions (Units : mm)



●Applications

Small signal low frequency amplifier
High speed switching

●Structure

NPN Silicon epitaxial planar transistor

●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SC5730	○	

●Absolute maximum ratings (T_a=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _c	1	A
	I _{CP}	2	A ^{*1}
Power dissipation	P _c	500	mW ^{*2}
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55~+150	°C

*1 P_w=10ms

*2 Each terminal mounted on a recommended land.

Transistor

●Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	30	—	—	V	$I_c=100\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	30	—	—	V	$I_c=1mA$
Emitter-base breakdown voltage	BV_{EBO}	6	—	—	V	$I_E=100\mu A$
Collector cut-off current	I_{CBO}	—	—	1.0	μA	$V_{CB}=20V$
Emitter cut-off current	I_{EBO}	—	—	1.0	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	150	300	mV	$I_c=500mA, I_b=50mA$
DC current gain	h_{FE}	120	—	390	—	$V_{CE}=2V, I_c=100mA$
Transition frequency	f_T	—	270	—	MHz	$V_{CE}=10V, I_E=-100mA, f=10MHz^{*1}$
Collector output capacitance	C_{ob}	—	10	—	pF	$V_{CB}=10V, I_E=0mA^{*2}, f=1MHz$
Turn-on time	T_{on}	—	30	—	ns	$I_c=1A, I_{b1}=0.1A$
Storage time	T_{stg}	—	120	—	ns	$I_{b2}=-0.1A$
Fall time	T_f	—	35	—	ns	$V_{CC}=25V$

*1 Non repetitive pulse

*2 See switching characteristics measurement circuits

● h_{FE} RANK

Q	R
120-270	180-390

●Electrical characteristic curves

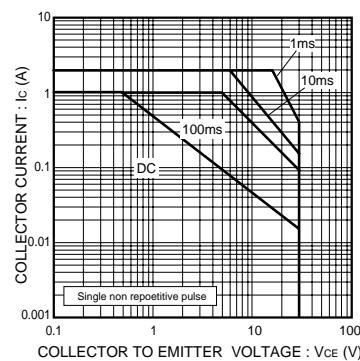


Fig.1 Safe operating area

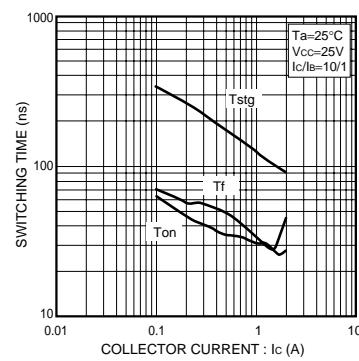


Fig.2 Switching Time

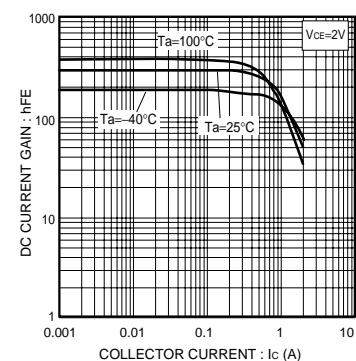


Fig.3 DC current gain vs. collector current

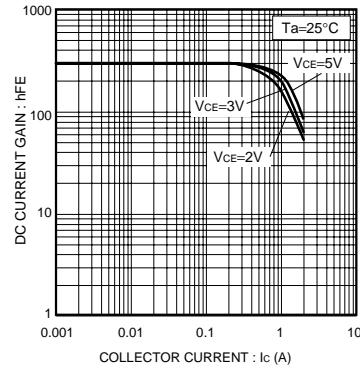


Fig.4 DC current gain vs. collector current

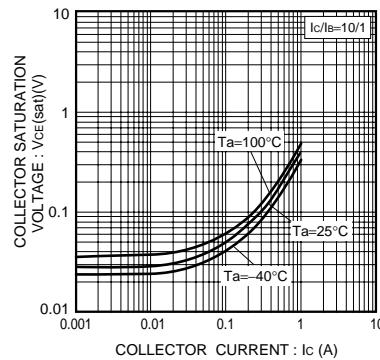


Fig.5 Collector-emitter saturation voltage vs. collector current

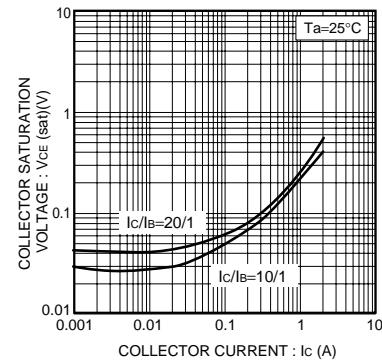


Fig.6 Collector-emitter saturation voltage vs. collector current

Transistor

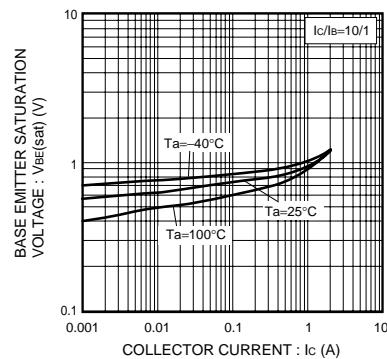


Fig.7 Base-emitter saturation voltage vs. collector current

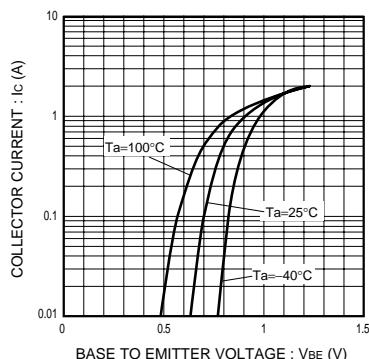


Fig.8 Ground emitter propagation characteristics

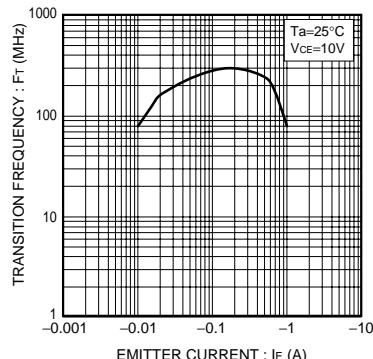


Fig.9 Transition frequency

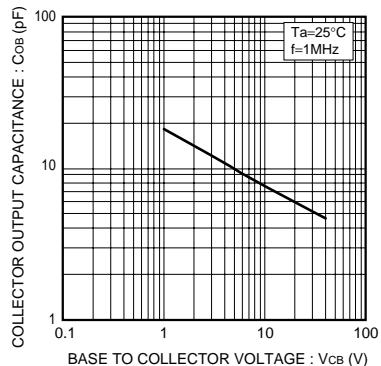
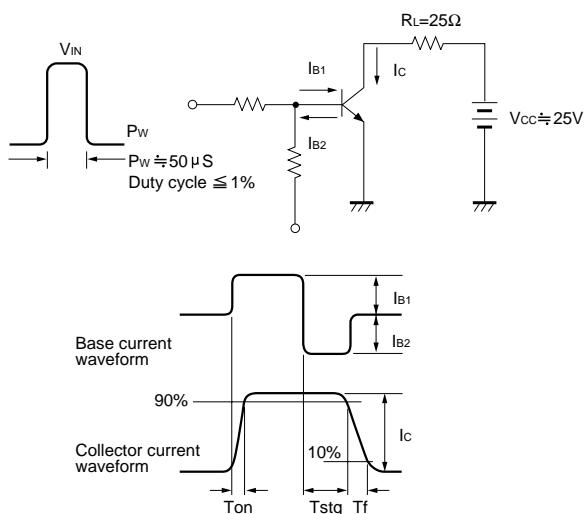


Fig.10 Collector output capacitance

●Switching characteristics measurement circuits



Appendix

Notes

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